Research Center for Photovoltaics



c-Si太陽電池セル裏面の腐食劣化態様 棚橋紀悟1·坂本 憲彦2·柴田 肇3·增田 淳1 <u>産業技術総合研究所 1太陽光発電研究センター、 2計量標準総合センター</u>

Background & Experimental Procedures

Background (1) (HAc = Ac	cetic Acid)	Background (2)	(HAc = Acetic Acid)	Experimental (1)	(HAc = Acetic Acid)	Experimental (2)	
Corrosion in Alumina Paste Layer (APL)		Proposed Corrosion Models		HAc-Vapor Exposure of Bare PV Cells		Localization of Series Resistance (R ₁)	
				Thick Glass Chamber ——	Whole planes of both	(a) Intact Contact	(b) Corroded Contact
				PV cell b) Hung PV cells	surfaces in a testing PV cell are uniformly surrounded by the applied stressors (temperature, humidity, and HAc vapor)	PV cell n-Si	PV cell
<u>25 °C / 45% rh, 2 months</u> <u>25 °C / 85% rh, 240 h</u> <u>25 °C / 8 with HAc</u>	<u>35% rh, 240 h</u> : Atmosphere			Saturated KCl aq. soln. +/- HAc (3%)	$\rightarrow \qquad \underline{Spatiotemporally} \\ \underline{harmonized power-loss and} \\ \underline{Rs-elevation are supposed} \\ \underline{loss} \\ loss$	$\begin{array}{c} & & & & \\ & & & \\ \hline \\ & & \\ &$	$\begin{array}{c} & & & & & \\ \hline \\$



Front Side Rear Side H. Xiong et al., "Corrosion behavior of crystalline silicon solar cells," Microelectron. Reliab., vol. 70, pp. 49-58, Mar. 2017.



Photovolt., vol. 8, no. 4, pp. 997–1004, Jul. 2018.



,with the respective AC equivalent circuits (under dark conditions) Rectangles colored in pink indicate the assumed locations of R_1 .

Summary

To address the origin of the elevated series-resistance ($R_{\rm S}$) that is a primary cause of corrosive degradation observed in fieldaged photovoltaic (PV) modules*, we evaluated the electrical characteristics of PV cells corroded with acetic acid (HAc) vapor.

The origin in $R_{\rm S}$ -elevation during corrosion of PV cells is fixed underneath front electrodes, from the following observations.

- (a) Evolution of EL-, $R_{\rm S}$ -, and visual-images during corrosion (Panel 1 to 3)
- (b) Effects of resistances in the Al bulk and the interconnector-busbar interface on power-loss (Panel 4 to 5)
- (c) Localization of $R_1 (\simeq R_S)$ in a corroded PV cell with single comb grid-fingers (Panel 6 to 9)

Because we have reported that Z_3 (a novel AC-impedance component that emerges during corrosive degradation) is also localized underneath the front electrodes**, it can be concluded that performance degradation with corrosion is preferentially caused by the evolution of electrical characteristics at this interface, but not at anyplace within a PV cell.

Tanahashi et al., *Tanahashi *et al*.. IEEE J. Photovolt., IEEE J. Photovolt., **9: 741-751 (2019) **8**: 997-1004 (2018)

A Convincing Demonstration

Degradation Profiles of PV Cells (with Different Compositions of Paste) Exposed to HAc Vapor at 85 °C / 80% rh



Results

Panel 1: Degradation Behavior

Degradation Profiles of a PV Cell Exposed to HAc Vapor

Panel 2: Degradation Behavior

Evolution of EL-, *R*_s-, and Visual-Images during Corrosion

Panel 3: Degradation Behavior	
Corrosion in Rear Surface	



Panel 4: Bulk Resistance

Busbar - Busbar Resistance (BBR)





Panel 5: Interface Resistance



Obvious enhancement of the resistance at solder joint is not confirmed, even when PV cells were nearly completely degraded with HAc vapor.

I, m, and Ac: see Panel 4



Panel 6: Identification of *R*₁**-Origin**

Preparation of a Cut Piece with Single-Comb Front Electrodes

(a) Preparation of Single-Comb Front Electrodes





Squares colored in orange, blue, and yellow indicate the scraped positions of the front electrodes

Panel 7: Identification of *R*₁-Origin





A, B, and C in the right graph indicate the respective interconnector-busbar pairs.

Panel 8: Identification of R₁-Origin

Assumed and Measured R₁ at Various Contacts

		-						
Contacted		Assumed R_1		$R_1(\Omega)$				
Terminals	Case A	Case B	Case C	Meas.	Case A			
FB-RB	$R_{1\mathrm{FB}}$	$R_{1 m R}$	$R_{1RB\parallel RC}$ ^a	0.945	0.007 b			
FB-RC	$R_{1 m FB}$	$R_{1 m R}$	$R_{1RB\parallel RC}$ ^a	0.868	0.907			
FC-RB	$R_{1 m FC}$	$R_{1 m R}$	$R_{1RB\parallel RC}$ ^a	0.724	0724 b			
FC-RC	$R_{1 m FC}$	$R_{1 m R}$	$R_{1RB\parallel RC}$ ^a	0.744	0.734			
FB-FC	$R_{1\rm FB} + R_{1\rm FC}$	pprox 0	pprox 0	1.404	1.641			
RB-RC	pprox 0	pprox 0	pprox 0	0.022	0.022			
^a $R_{1PP} = R_{1PP}$ denotes the resistance in a parallel circuit with R_{1PP} and R_{1PC} [i.e.								

 $\kappa_{1RB}||_{RC}$ denotes the resistance in a parameteric uncult with κ_{1RB} and κ_{1RC} [i.e., $R_{1\text{RB}\parallel\text{RC}} = (R_{1\text{RB}} \times R_{1\text{RC}}) / (R_{1\text{RB}} + R_{1\text{RC}})].$

^b These values indicate the respective mean resistances in FB-RB/RC and FC-RB/RC contacts.

Actual data completely agree with those assumed in Case A.

Panel 9: Identification of *R*₁**-Origin**



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